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Infrared Applications of Semiconductors II

Editors: Donald L. McDaniel, M. Omar Manasreh, Richard H. Miles and Sivalingam Sivananthan

Index

[More information](#)

AUTHOR INDEX

- Abramof, E., 389, 661
 Ahearn, J.S., 31
 Ahlswede, E., 123
 Ahn, Byung Tae, 655
 Ahoujja, M., 129
 Alfer, E.H., 95
 Akashi, Yoshito, 601
 Akimov, B.A., 359
 Allerman, A.A., 19
 Alvarez, A., 625
 Andreev, A.C., 117
 Anson, S.A., 83
 Antoszewski, J., 353
 Apotovsky, B., 291
 Aqariden, F., 377
 Ashley, T., 143, 153
 Augustine, F.L., 267
 Avella, M., 625

 Bachmann, K.J., 507
 Baek, J-H., 649
 Bajaj, K.K., 57
 Bakken, D.W., 335
 Bandara, S.V., 205
 Bandeira, I.N., 389, 661
 Barber, H.B., 267
 Barbier, L., 285
 Barnes, S.L., 233
 Barrett, H.H., 267
 Barthelmy, S.D., 285
 Baucom, K.C., 19
 Beckham, C., 13
 Beeman, J.W., 215
 Belogorokhov, A.I., 301, 383
 Belogorokhova, L.I., 383
 Bennett, B.R., 11
 Bennett, P., 273
 Berding, M.A., 341
 Bewley, W.W., 95
 Bhaskar, S., 365
 Bichl, H., 165
 Biefeld, R.M., 19
 Bieg, B., 611
 Bishop, S.G., 205
 Bist, H.D., 365
 Bliss, D.F., 491
 Boggess, Thomas F., 83
 Bogoyavlenskiy, V.A., 359
 Boschetti, C., 389, 661
 Bose, P.K., 555, 673, 679
 Bower, J.R., 135
 Boyer, J.R., 45
 Brincat, Andrea, 441
 Brown, G.J., 129, 531
 Bründermann, E., 177
 Brunett, B.A., 241, 253
 Bryant, G., 491
 Bulsara, M.T., 631

 Burger, A., 365
 Butler, J.F., 291
 Byer, Robert L., 481

 Cabelli, C., 221
 Cairns, J.W., 143
 Case, F.C., 233
 Cederberg, J.G., 611
 Chamberlin, D.R., 177
 Chan, K.S., 413
 Chan, Michael C.Y., 413, 425
 Chandra, D., 377
 Chang, Y.C., 205
 Chao, I., 371
 Charache, G.W., 37
 Chauvet, M., 491
 Chavez, J.R., 637
 Chen, E., 31
 Chen, K-T., 365
 Cho, J., 419
 Choi, H.K., 37
 Choi, S.G., 419
 Choi, W.J., 419
 Chong, T.C., 617
 Chou, L.J., 205
 Chow, D.H., 95
 Choy, W.C.H., 453
 Chu, Hye Yong, 607, 655
 Chuang, S.L., 205
 Closs, H., 389, 661
 Cooke, P., 13
 Costales, A., 525
 Cox, J.A., 135
 Cross, J.O., 11
 Curti, M., 625
 Curtis, A.P., 205

 Dat, R., 377
 de la Puente, E., 625
 Dell, J.M., 353
 Dereniak, E.L., 267
 Dhar, N.K., 329
 Dinetta, L.C., 135
 Dong, Jie, 643
 Doty, F.P., 291
 Du, A.Y., 617
 Dubon, O.D., 177
 Duncan, W.M., 377

 Ehrenreich, H., 191
 Eissler, Elgin E., 309
 Elliott, C.T., 143
 Ershov, O.G., 101
 Eskin, J.D., 267
 Evwaraye, A.O., 581

 Falcon, M., 107
 Fang, X.M., 371

Cambridge University Press

978-1-107-41342-9 - Materials Research Society Symposium Proceedings: Volume 484:

Infrared Applications of Semiconductors II

Editors: Donald L. McDaniel, M. Omar Manasreh, Richard H. Miles and Sivalingam Sivananthan

Index

[More information](#)

- Faraone, L., 353
 Fathimulla, Ayub, 573
 Feigelson, Robert S., 481
 Fejer, Martin M., 481
 Felix, C.L., 95
 Feng, M., 205
 Feng, Z.C., 13, 63
 Ferguson, I., 13, 63
 Fernelius, N.C., 549, 567
 Ferreira, S.O., 389, 661
 Fitzgerald, E.A., 631
 Flatté, Michael E., 71, 83
 Flint, J.P., 319, 335
 Flynn, C.J., 495
 Fornari, R., 625
 Friesenhahn, S.J., 291
 Fuchs, F., 123
 Fukuyama, Atsuhiko, 601
- Gal, M., 397
 Gass, Richard G., 437
 Gehrels, N., 285
 Ghatak, Kamakhya P., 555, 673, 679
 Gianardi, Jr., D.M., 107
 Gianordoli, S., 165
 Gilbert, T.S., 241, 253
 Gill, J., 205
 Glass, H.L., 319, 335
 Goldberg, L., 95
 Gonzalez, M.A., 625
 Goorsky, M.S., 241
 Gordon, Leslie A., 481
 Gornik, E., 165
 Grein, C.H., 71, 83, 191
 Guha, Shekhar, 573
 Gunapala, S.D., 205
 Gupta, Sandhya, 183
- Haines, W.T., 45
 Haller, E.E., 177, 215
 Halliburton, L.E., 549
 Han, I.K., 419
 Han, S.M., 419
 Han, W.S., 649
 Hansen, W.L., 215
 Hasenberg, T.C., 83
 Hawkins, S.A., 491
 Heffelfinger, J.R., 247
 Helm, M., 165
 Hermon, H., 241
 Herres, N., 123
 Heyman, J.N., 165
 Himpfel, F.J., 589
 Ho, Kai-Ming, 183
 Hoenshel, K., 637
 Hong, W., 205
 Hopkins, F.K., 567
 Hopkins, R.H., 567
 Hsieh, K.C., 205
 Hu, K., 285
 Huang, J-W., 611
 Hvozdar, L., 165
- Ikari, Tetsuo, 601
 Imenkov, A.N., 101
 Ivanchik, I.I., 301
 Iyer, S., 57
- Jackson, Howard E., 437, 543
 Jagadish, C., 397
 James, R.B., 241, 247, 253
 Jang, D-J., 83
 Jefferies, R., 143
 Jeong, B.S., 649
 Jimenez, J., 625
 Johnson, A.D., 143
 Jones, J., 495
- Kajihara, N., 347
 Kang, K.N., 419
 Karunasiri, Gamani, 459
 Katiyar, R.S., 365
 Kato, Kiyoshi, 475
 Kawata, S., 347
 Kemp, W.T., 637
 Khokhlov, D.R., 295, 301, 383
 Kim, H.J., 419
 Kim, S., 205
 Kim, S.H., 419
 Kost, A.R., 3
 Krizmanic, J.F., 285
 Kruck, P., 165
 Kuech, T.F., 589, 611
 Kumagai, M., 595
 Kurtz, S.R., 19
- Launois, H., 447
 Le, H.Q., 107
 Lee, Alex S.W., 459
 Lee, B., 649
 Lee, E-H., 607, 649
 Lee, J.I., 419
 Lee, K-S., 607
 Lee, S., 419
 Lehtonen, S.J., 285
 Leitz, C., 631
 Lesko, J.D., 135
 Li, E. Herbert, 425, 431, 459
 Li, J., 57
 Li, K., 63
 Li, M.F., 617
 Lin, Chih-Hsiang, 89, 107, 129
 Lin, J.Y., 63
 Lingren, C.L., 291
 Linhart, A.M., 177
 Liu, H.C., 205
 Liu, J.K., 205
 Lo, Kai-Ming, 467
 Lund, J.C., 241, 253
 Luong, E., 205
 Lynn, K.G., 319
- Mach, K.J., 285
 Maeda, Kouji, 601
 Maffetone, John, 519

Cambridge University Press

978-1-107-41342-9 - Materials Research Society Symposium Proceedings: Volume 484:

Infrared Applications of Semiconductors II

Editors: Donald L. McDaniel, M. Omar Manasreh, Richard H. Miles and Sivalingam Sivananthan

Index

[More information](#)

- Majumder, Gautam, 555, 673, 679
 Man, W.M., 431
 Manasreh, M.O., 637
 Mangalam, B., 57
 Marable, M., 567
 Mares, P.J., 205
 Marks, D.G., 267
 Matherson, K.J., 267
 Matsumoto, Koh, 643
 Mauk, M.G., 135
 McCann, P.J., 371
 McDaniel, Jr., D.L., 107
 McKelvey, M., 205
 Medlin, D.L., 247
 Meisen, P., 259
 Meyer, J.R., 95, 487
 Meyer, R., 567
 Micallef, Joseph, 441
 Mikhailova, M.P., 101
 Missous, M., 637
 Mitchel, W.C., 129
 Mitra, P., 233
 Miyamoto, Y., 347
 Moiseev, K.D., 101
 Moore, W.J., 11
 Motisuke, P., 389, 661
 Mui, P., 567
 Mula, Guido, 171
 Mulugeta, S., 57
 Mumulo, J., 205
 Murry, S.J., 89, 107
 Musca, C.A., 353
- Nathan, Vaidya, 667
 Nichols, K., 31
- Oakley, D.C., 37
 O'Brien, W.L., 589
 O'Dette, P., 233
 Oganessian, A., 291
 Ohmer, Melvin C., 525, 531, 543, 573, 581
 Olesberg, J.T., 71, 83
 Olsen, C.S., 215
 Ortiz, V., 171
- Paine, D.C., 31
 Palmer, D., 285
 Pandey, Ravindra, 525
 Park, Hyo-Hoon, 607, 655
 Park, Min Soo, 655
 Parsons, A.M., 285
 Peanasky, M.J., 611
 Pei, S.S., 89, 107
 Pelczynski, M., 13, 63
 Pelekanos, N.T., 171
 Pépin, A., 447
 Perera, A.G.U., 199
 Perrin, Ronald E., 573
 Phillips, C.C., 487
 Pi, B., 291
 Pidduck, A.J., 143
 Piotrowski, J., 353
- Pletschen, W., 123
 Poirier, Derrick M., 519
 Pollak, T.M., 543, 549
 Pool, F., 205
 Pryce, G.J., 143
- Rai, Brajesh K., 365
 Rao, E.V.K., 447
 Rappl, P.H.O., 389, 661
 Rar, A., 259
 Rea, Laura S., 573
 Recio, J.M., 525
 Reichertz, L.A., 177
 Reine, M.B., 233
 Röser, H.P., 177
 Route, Roger K., 481
 Ruderman, Warren, 519
 Ryabova, L.I., 359
- Sachar, H.K., 371
 Saito, M., 595
 Saker, M.K., 495
 Salamanca-Riba, L., 329
 Salamo, G.J., 491
 Sanz, L.F., 625
 Schaff, W., 199
 Schieber, M., 241
 Schlesinger, T.E., 253
 Schmitz, J., 123
 Schneider, M., 447
 Schunemann, Peter G., 531, 537, 543, 549
 Seelmann-Eggebert, M., 259
 Segev, M., 491
 Selvig, E., 95
 Sengupta, D.K., 205
 Seo, Dong Ju, 589
 Setzler, S.D., 549
 Shah, S.I., 419
 Shanabrook, B.V., 11
 Shellenbarger, Z.A., 135
 Shen, W.Z., 199
 Sher, A., 341
 Shi, Z.Q., 285
 Shih, H.D., 377
 Shiu, Wai-Chee, 441
 Shu, P., 285
 Sigalas, Mihail, 183
 Siliquini, J.F., 353
 Sims, P.E., 135
 Singh, N.B., 567
 Sirmain, G., 177
 Small, David L., 537
 Smith, E.P.G., 353
 Smith, J.M., 649
 Smith, P.C., 495
 Smith, S.R., 581
 Smout, A.B.J., 143
 Snodgrass, S.J., 285
 Socha, A.J., 335
 South, J.D., 135
 Speziale, V.M., 335
 Stahle, C.M., 285

Cambridge University Press

978-1-107-41342-9 - Materials Research Society Symposium Proceedings: Volume 484:

Infrared Applications of Semiconductors II

Editors: Donald L. McDaniel, M. Omar Manasreh, Richard H. Miles and Sivalingam Sivananthan

Index

[More information](#)

- Stall, R.A., 13, 63
 Stenstrom, C.C., 273
 Stevens, K.T., 549
 Stillman, G.E., 205
 Stockman, S.A., 611
 Strasser, G., 165
 Sudharsanan, R., 273
 Sugiyama, I., 347
 Suhre, D., 567
 Sun, Jingxi 589
 Szeles, Csaba, 309, 319
 Szmulowicz, F., 129
- Tan, H.H., 397
 Tan, K.L., 63
 Tanaka, Eiko, 475
 Tanner, M.O., 199
 Taylor, L.L., 495
 Tennant, W.E., 221
 Timmons, M.L., 507
 Tlali, Spirit, 543
 Tobin, S.P., 233
 Torezan, J., 205
 Tuttle, Gary, 183
- Ubukata, Akinori, 643
 Uekusa, S., 595
 Ueta, A.Y., 389, 661
 Unterrainer, K., 165
 Uppal, P., 31
- Vakerlis, G.D., 273
 Van Scyoc, J.M., 241, 253
 Vasil'kov, V.N., 359
 Venkatraman, S., 57
 Vere, A.W., 495
 Vieu, C., 447
 Vodopyanov, K.L., 487, 561
- Vurgaftman, I., 95, 487
- Wakutani, M., 595
 Walther, M., 123
 Wang, C.A., 37
 Wang, K.L., 199
 Wang, W.I., 205
 Weber, M., 319
 Wee, A.T.S., 63
 Wei, H-Y., 329
 Weimar, U., 123
 Weiss, B.L., 453
 Woo, D.H., 419
 Woolfenden, J.M., 267
 Wu, H., 89
 Wu, YewChung Sermon, 481
- Yakovlev, Yu.P., 101
 Yan, Chi, 107
 Yang, B.H., 89
 Yang, M.J., 11
 Yang, Rui Q., 89, 107
 Yoo, Byueng-Su, 655
 Yoon, H., 241, 253
 Yoshino, Kenji, 601
 Young, E.T., 267
 Yu, Phil Won, 573
 Yu, S.F., 431
 Yuan, S., 397
- Zelman, David E., 519
 Zelmon, David E., 537
 Zhang, D., 89
 Zhang, Z., 617
 Zhao, S., 291
 Zheng, Dong, 481
 Zhurtanov, B.E., 101
 Zimmermann, H., 259

Cambridge University Press

978-1-107-41342-9 - Materials Research Society Symposium Proceedings: Volume 484:

Infrared Applications of Semiconductors II

Editors: Donald L. McDaniel, M. Omar Manasreh, Richard H. Miles and Sivalingam Sivananthan

Index

[More information](#)

SUBJECT INDEX

- γ -ray
 - detectors, 309, 335
 - irradiation, 631
- ab initio* calculations, 341
- activation energy, 581
- AgGaS₂, 525
- Al_{0.7}Ga_{0.3}As:Er,N,O, 595
- AlGaAs/GaAs, 453
- AlGaAs/GaAsP, 413
- Al_{0.5}Ga_{0.5}As_{1-y}Sb_y buffer layers, 31
- amphoteric, 341
- annealing, 353, 447
- anodic-induced intermixing, 397
- array, 285
- asymmetric double quantum wells, 487
- atomistic model, 525
- auger, 525
 - electron spectroscopy (AES), 63
 - recombination, 3, 71, 83, 117
 - suppressing, 191
- avalanche photodiodes, 135
- bandgap engineering, 233
- band-structure engineering, 191
- barium titanate, 537
- binding energies, 525
 - hole, 525
- Bridgman growth, 45, 335
- broken-gap alignment, 101
- bulk
 - single crystals, 45
 - specimens, 673
- Burstein-Moss shift, 667, 673
- cadmium zinc telluride (CZT), 253, 257, 335
- CaF₂, 661
- CaF₂/Si, 661
- capacitance voltage (CV), 581
- capping film, characteristics of, 419
- carrier
 - depletion, 191
 - dispersion laws, 673
- cascade lasers, 89
- CdGeAs₂, 475, 507, 531, 581
- Cd_{1-x}Zn_xTe, 241, 247
- CdZnTe, 291, 309
 - detector, 319
 - strip detector, 285
- CH₄/H₂, 259
- chalcopyrite, 531
- charge collection, 241
- chemical bonding, 589
- CO₂ lasers, 573
- complex
 - defects, 347
 - related traps, generation of, 595
- composition control, 377
- compositional modulations, 31
- compositionally graded buffers, 631
- continuous wave, 177
- critical layer thickness, 425
- crystallinity, 241
- data visualization, 253
- deep-level
 - transient
 - Fourier spectroscopy (DLTFS), 347
 - spectroscopy (DLTS), 611
 - traps, 347
- defect(s), 481
 - density, 329
 - semiconductors, 491
- detector, 291, 383
- dielectric cap quantum-well disordering (DCQWD), 419
- diethylaluminum ethoxide, 611
- diffused quantum wells, 431
- diffusion bonded, 573
- diodes(s), 123
 - lasers, 3
- directional couplers, 467
- dislocation, 377, 425, 617
- distributed Bragg reflector (DBR), 649
 - feedback lasers, 643
- donor levels, 525
- doping, 673, 679
 - heavy, 679
- double(-)
 - barrier structures (DBS), 607
 - crystal x-ray diffraction, 241
- dry etching, 259
- dual band, 205
- effective dielectric functions, 377
- EL2, 601
- EL6, 601
- electroluminescence, 165
- electron(-)
 - concentration, 555
 - cyclotron resonance (ECR), 259
 - nuclear double resonance (ENDOR), 549
 - paramagnetic resonance (EPR), 549
- electrothermal instabilities, 359
- emission, 165
- epitaxial
 - films, 199
 - relations, 661

Cambridge University Press

978-1-107-41342-9 - Materials Research Society Symposium Proceedings: Volume 484:

Infrared Applications of Semiconductors II

Editors: Donald L. McDaniel, M. Omar Manasreh, Richard H. Miles and Sivalingam Sivananthan

Index

[More information](#)

- Er(-)
 - laser pulses, 561
 - related emission, 595
- ESCA, 525
- etch pit density, 241
- fabrication, 285
- far-IR, 177, 199
- Fe-doped InP, 625
- film thickness, 555, 673, 679
- filters, 183
- final-state optimization, 71
- focal-plane array, 295
- fourth-harmonic generation, 567
- free carrier absorption, 199
- frequency conversion devices, 537
- FTIR, 3
- GaAs, 199, 573
 - (100) surfaces, 589
 - wafer-bonded structure, 481
- GaAs/AlGaAs, 397
 - material, 165
 - multiple quantum well, 419
 - quantum-well heterostructures, 447
- GaInAsSb, 37, 135
- Ga_{0.51}In_{0.49}P/GaAs, 441
- Ga_{1-x}In_xSb, 45
- gamma ray, 285, 291
- GaSb, 57
- GaSe, 567
- gate-controlled, 123
- geometric factors, 655
- germanium, 177
 - blocked impurity band (BIB), 215
- grain boundaries, 241, 247
- heterojunction, 101
- Hg vacancies, 347
- Hg_{1-x}Cd_xTe, 377, 667
- HgCdTe, 221, 233, 341, 353, 679
 - detectors, 233
 - IR photodiodes, 329
- high temperature, 191
- high-pressure Bridgman (HPB), 309
- high-resolution x-ray diffraction, 389
- hole carrier collection, 319
- III-V, 143
- II-IV-V₂ chalcopyrite, 507
- II-VI, 673
- image intensifier, 221
- implantation, 437
- improved resolution, 319
- impurity densities, 341
- in situ* laser reflectometry, 649
- In_{0.5}(Al_xGa_{1-x})_{0.5}P, 611
- InAsAsSb, 117
- InAs/GaInSb, 3, 71, 123
- InAs/In_xGa_{1-x}Sb, 129
- InAs/InGaSb/InAs/AlSb, 11, 107
- InAsSb/InAsP, 19
- InAsSbP, 135
- indium antimonide (InSb), 13, 63, 143, 153
- InGaAs/AlGaAs multiple quantum wells, 631
- InGaAs/InP, 425
- InGaAsP, 13, 679
- InGaAsSb, 3
- initial nucleation mechanism, 329
- InSb, 13, 63, 143, 153
- InSb/InAlSb diodes, 143
- interband transitions, 667
- interdiffused quantum-well laser, 413
- interdiffusion, 413, 425, 437, 441, 453, 467
 - mechanisms, 447
- interface, 63
- intermixed lasers, 397
- intermixing enhancement, 447
- intersubband, 459
 - absorption, 71
 - quantum well, 165
 - transitions, 637
- inter-valence band absorption, 3
- In_xGa_{1-x}As, 631
- ion implantation, 397, 595
- ionizing radiation, 253
- IR, 123, 153, 171, 383, 567
 - band-reject filters, 183
 - detection, 129
 - detector, 301
 - microscopy, 241
 - NLO material, 507
 - photodetectors, 295
- IV-VI, 673
- laser(s), 177
 - damage, 525
- lattice(-)
 - defects, 495
 - matched GaAs/AlGaAs quantum well, 205
 - mismatched heterostructures, 617
 - vibrations, 383
- LBIC, 353
- lead telluride (PbTe), 295, 301
- leakage currents, 241
- LEDs, 143
- light modulation, 171
- liquid-phase epitaxy (LPE), 215, 371
- local compensation, 625
- localized states, 607
- long wave IR, 205
- longitudinal optical (LO) phonons, 365
- low-light-level, 221
- magnetic field, parallel, 673
- MBE, 57
 - growth, 11

Cambridge University Press

978-1-107-41342-9 - Materials Research Society Symposium Proceedings: Volume 484:

Infrared Applications of Semiconductors II

Editors: Donald L. McDaniel, M. Omar Manasreh, Richard H. Miles and Sivalingam Sivananthan

Index

[More information](#)

- mechanical cracks, 241
- medical imaging, 285
- mercury cadmium telluride, 153
- metallic
 - meshes, 183
 - photonic bandgap, 183
- metalorganic
 - chemical vapor deposition (MOCVD), 13, 19, 643, 649
 - vapor-phase epitaxy (MOVPE), 233
- metastable transition, 601
- mid(-)
 - IR, 3, 89, 95, 101, 143, 531, 561
 - detectors, 135
 - lasers, 11, 19, 83
 - MQW laser, 117
 - (3–6 μm) lasers, 19
 - wave IR, 205
- molecular-beam epitaxy (MBE), 329, 371, 377, 389, 617, 661
- MOVPE, 233
- multiplexer readout, 267
- multistage injection lasers, 19
- native point defect, 341
- near-room temperature, 221
- negative luminescent, 153
 - sources, 143
- Nomarski microscopy, 63
- nonlinear optical, 567
 - (NLO) material, 507, 525, 555, 581
 - susceptibility, 531
- nonradiative recombination, 601
- nonstoichiometry, 495
- nuclear medicine imaging, 267
- optical
 - absorption, 495, 667
 - gain, 413
 - losses, 481
 - parametric
 - generator (OPG), 561
 - oscillation, 573
 - oscillator (OPO), 495, 537
 - recovery, 601
- optically pumped, 95
 - laser, 107
- organometallic
 - chemical vapor deposition (OMCVD), 507
 - vapor-phase epitaxy (OMVPE), 37, 631
- oxygen, 611
- passivant, 589
- patterning of $\text{SiO}_2/\text{Si}_3\text{N}_4$ epilayers, 447
- PbSe, 371
- $\text{Pb}_{1-x}\text{Sn}_x\text{Se}$
- PbTe/SnTe superlattices, 389
- periodically poled, 537
- phase modulator, 453
- phase-matched, 487
- phonons, 383
- photoacoustic, 601
- photo-assisted resonant tunneling, 607
- photoconductivity, 301
 - kinetics, 359
- photoemission, 555
 - current density, 555
- photoluminescence, 37, 459, 595
 - spectroscopy (PL), 365
- photon
 - energy, 555
 - recycling, 191
- photoreflectance (PR), 57
- photorefractive semiconductor, 491
- photoresponse, 129, 531
- piezoelectric, 601
 - heterostructure, 171
- p-i-n devices, 273
- p-InGaAs/GaAs, 617
- pipes, 309
- point defects, 495, 549
- polarization, 531
 - properties, 655
- polyimide, 183
- population inversion, 177
- p-type dopant, 37
- pulse height analysis, 253
- quantum(-)
 - cascade, 165
 - confinement, 555
 - dots, 555, 673, 679
 - efficiencies, 89
 - well, 95, 425, 441, 453, 467, 555, 643
 - intermixing, 397, 441
 - IR photodetector (QWIP), 205, 459
 - wires, 555
 - wires, 679
- quasi-phase-matched (QPM), 481, 573
- quaternary materials, 679
- radiation detector, 253, 273
- Raman scattering, 543
 - spectroscopy, 365
- reactive ion etching (RIE), 353
- reciprocal space maps, 389
- refractive index, 537
- resistivity, 253
- resonant tunneling diode (RTD), 607
- responsivity spectra, 459
- room-temperature radiation detectors, 291
- scanning
 - photocurrent (SPC), 625
 - photoluminescence (SPL), 625
- second-harmonic generation (SHG), 475, 481, 487, 567, 573
- selenium disulfide, 589

Cambridge University Press

978-1-107-41342-9 - Materials Research Society Symposium Proceedings: Volume 484:

Infrared Applications of Semiconductors II

Editors: Donald L. McDaniel, M. Omar Manasreh, Richard H. Miles and Sivalingam Sivananthan

Index

[More information](#)

- self-trapping of optical beams, 491
- Sellmeier equation, 475
- semiconductor, 143, 383
 - detectors, 257
 - diode laser, 101
 - laser, 89, 643
 - multiple-electrode detectors, 291
- semi-insulating (SI), 309
- 7.5–14 μm , 205
- Si, 199
 - (100), 371
 - (211) substrates, 329
- silver gallium sulfide, 525
- single(-)
 - crystal(s), 525
 - AgSe, 365
- SiN_x
 - capping layer, 419
 - hydrogen content in, 419
- SiO_2 capping, 447
- spatial
 - mapping, 253
 - nonuniformity, 495
 - solitons, 491
- spectral ellipsometry, 377
- strain, 441, 643
- strained, 459
 - InGaAs/AlGaAs, 205
- structural
 - characterization, 389
 - defects, 241
- substrate misorientation, 37
- sum frequency generation (SHG), 475
- superlattice, 83, 123, 129, 437
- surface, 63
 - defects, 377
 - interdiffusion, 543
- synchrotron radiation photoemission spectroscopy, 589
- Te(-)
 - doped, 57
 - inclusions, 309
 - precipitates, 247
- TEES, 319
- tensile strain, 413
- ternary
 - chalcopyrite, 581
 - materials, 679
- thermal
 - admittance spectroscopy (TAS), 581
 - images, 153
 - stress, 447
- thermally stimulated currents (TSC), 359
- thermo-optic dispersion formula, 475
- thermovoltaic, 45
 - devices, 37
- threading, 31
- 3–5.3 μm , 205
- tilted pillar structures, 655
- transient charge technique, 253
- transition energy, 57
- transmission electron microscopy, 247
- traps, 617
- traveling-wave optical parametric generator, 561
- triple axis x-ray diffraction, 241
- turbo disk, 13
- twin(s), 241
 - boundaries, 247
- two-color IR detector, 233
- type(-)
 - conversion, 353
 - II, 11, 95
 - quantum well, 107
 - superlattice, 3
- ut-products, 319
- vertical-cavity surface-emitting laser (VCSEL), 95, 431, 649, 655
- voids, 377
- wafer bonding, 481
- waveguides, 467
- x-ray, 309
 - diffraction, 661
 - photoelectron spectroscopy (XPS), 63
 - reflectometry, 661
- zinc(-)
 - composition, 241
 - vacancy, 549
- ZnGeAs_2 , 507
- ZnGeP_2 , 495, 525, 549
 - single crystals, 543
- ZnSe , 365
- 0.98 μm emission, 595